

ME2310-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)			
30	0.030 at V _{GS} = 10 V	6.5	4.5 nC			
	0.033 at V _{GS} = 4.5 V	6.0	4.5110			

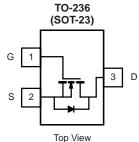
FEATURES

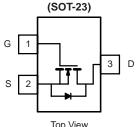
- Halogen-free According to IEC 61249-2-21 ٠ Definition
- TrenchFET[®] Power MOSFET ٠
- 100 % R_g Tested ٠
- Compliant to RoHS Directive 2002/95/EC ٠

APPLICATIONS

DC/DC Converter







G S N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	± 20	v	
	T _C = 25 °C		6.5 ^a		
Continuous Drain Current ($T_1 = 150 \ ^{\circ}C$)	T _C = 70 °C	I _D	6.0		
	T _A = 25 °C	טי	5.3		
	T _A = 70 °C		5.0	A	
Pulsed Drain Current		I _{DM}	25		
	T _C = 25 °C		1.4		
Continuous Source-Drain Diode Current	T _A = 25 °C	۱ _S	0.9 ^{b, c}		
	T _C = 25 °C		1.7		
Maximum Power Dissipation	T _C = 70 °C	PD	1.1	W	
	T _A = 25 °C	· D	1.1 ^{b, c}	vv	
	T _A = 70 °C		0.7 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		
Soldering Recommendations (Peak Tempera	ature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	90	115	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	60	75	0/11		

Notes:

a. Package limited

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 130 °C/W.

SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static	•				•	•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = 250 \mu A$	30			V		
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	l _D = 250 μΑ		31		mV/°C		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	η = 250 μΑ		- 5				
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.7	1.1	2.0	V		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA		
Zaro Cata Valtaga Drain Current	1	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$			10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	10			Α		
	Р	V _{GS} = 10 V, I _D = 3.2 A		0.030		0		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 2.8 A		0.033		Ω		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 4.8 A		11		S		
Dynamic ^b	-1							
Input Capacitance	C _{iss}			335		pF		
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		45				
Reverse Transfer Capacitance	C _{rss}			17				
Tatal Cata Charge	0	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 3.4 \text{ A}$		4.5	6.7	-		
Total Gate Charge	Qg			2.1	3.2			
Gate-Source Charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 3.4 A		0.85				
Gate-Drain Charge	Q _{gd}			0.65				
Gate Resistance	Rg	f = 1 MHz	0.8	4.4	8.8	Ω		
Turn-On Delay Time	t _{d(on)}			12	20			
Rise Time	t _r	V_{DD} = 15 V, R _L = 5.6 Ω		50	75	-		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ 2.7 A, V_GEN = 4.5 V, R_g = 1 Ω		12	20			
Fall Time	t _f			22	35			
Turn-On Delay Time	t _{d(on)}			5	10	ns		
Rise Time	t _r	V_{DD} = 15 V, R _L = 5.6 Ω		12	20	-		
Turn-Off Delay Time	t _{d(off)}	${\rm I}_{\rm D}{\cong}2.7$ A, ${\rm V}_{\rm GEN}$ = 10 V, ${\rm R}_{\rm g}$ = 1 Ω		10	15			
Fall Time	t _f			5	10			
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			1.4	A		
Pulse Diode Forward Current	I _{SM}				15			
Body Diode Voltage	V _{SD}	$I_{S} = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V		
Body Diode Reverse Recovery Time	t _{rr}			10	20	ns		
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 2.7 A, dl/dt = 100 A/μs, T _J = 25 °C		5	10	nC		
Reverse Recovery Fall Time	t _a	$F = 2.7 \text{ A, u/u} = 100 \text{ A/}\mu\text{s, } 1\text{ J} = 25 \text{ C}$		6				
Reverse Recovery Rise Time	t _b	-1		4		ns		

Notes:

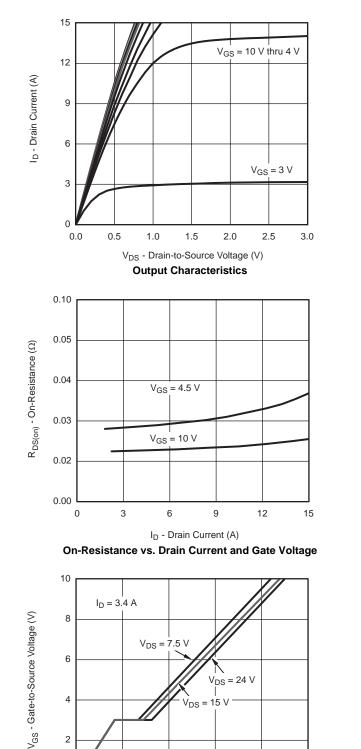
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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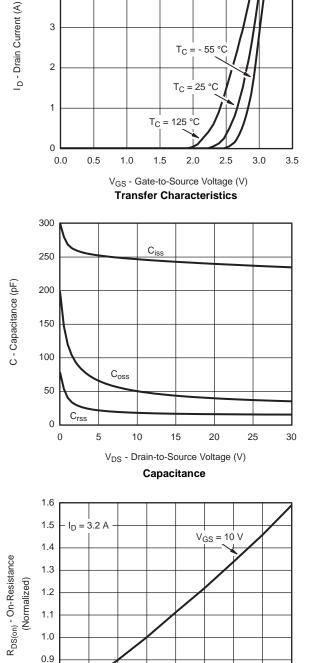
Qg - Total Gate Charge (nC)

Gate Charge

4

5

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



5

4

0.8

0.7

- 50

- 25

0

25

50

T_J - Junction Temperature (°C) On-Resistance vs. Junction Temperature

75

100

125 150



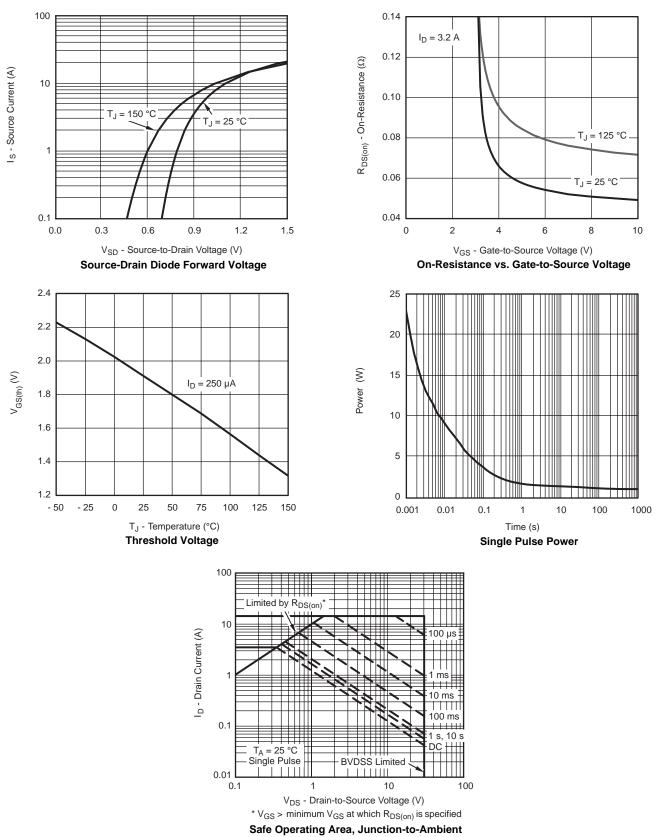
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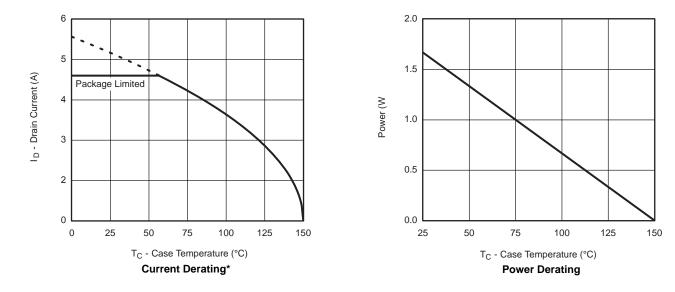
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.







Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
C	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01				



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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